

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

CN4156
CN4157
CN5179

FORWARD REFERENCE DIODE
(STABISTOR)

AXIAL LEAD EPOXY CASE

DESCRIPTION

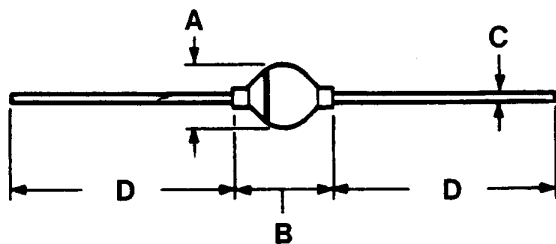
The CENTRAL SEMICONDUCTOR CN4156 series types are multi-chip silicon diodes mounted in a cost effective epoxy axial leaded case designed for applications requiring controlled forward voltage characteristics such as voltage regulation, sensing, and comparing. This series is a replacement for the 1N4156, 1N4157, and 1N5179, respectively. Special selections of DC parameters including V_F (forward voltage drop) at various test conditions are available on special order.

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$)

	SYMBOL		UNIT
Power Dissipation	P_D	400	mW
Operating and Storage Junction Temperature	T_J, T_{STG}	-65 TO +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
V_F (CN4156)	$I_F=1.0\text{mA}$	1.21	1.41	V
V_F (CN4156)	$I_F=10\text{mA}$	1.38	1.58	V
V_F (CN4156)	$I_F=100\text{mA}$	1.54	1.84	V
V_F (CN4157)	$I_F=1.0\text{mA}$	1.85	2.05	V
V_F (CN4157)	$I_F=10\text{mA}$	2.12	2.32	V
V_F (CN4157)	$I_F=100\text{mA}$	2.36	2.66	V
V_F (CN5179)	$I_F=1.0\text{mA}$	2.20	2.80	V
V_F (CN5179)	$I_F=10\text{mA}$	2.60	3.20	V
V_F (CN5179)	$I_F=100\text{mA}$	3.00	3.70	V
I_R	$V_R=20\text{V}$		10	μA



	INCHES		mm	
	MIN	MAX	MIN	MAX
A	-	.140	-	3.56
B	-	.200	-	5.10
C	.012	.016	0.30	0.40
D	.750	-	19.0	-